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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	121
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 15x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5606bk0mlq6r

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PC[5]	PCR[37]	AF0 AF1 AF2 AF3 —	GPIO[37] SOUT_1 CAN3TX DEBUG[3] EIRQ[7]	SIUL DSPI_1 FlexCAN_3 SSCM SIUL	I/O O O O I	M	Tristate	91	130	158
PC[6]	PCR[38]	AF0 AF1 AF2 AF3	GPIO[38] LIN1TX E1UC[28] DEBUG[4]	SIUL LINFlex_1 eMIOS_1 SSCM	I/O O I/O O	S	Tristate	25	36	44
PC[7]	PCR[39]	AF0 AF1 AF2 AF3 — —	GPIO[39] — E1UC[29] DEBUG[5] LIN1RX WKUP[12][4]	SIUL — eMIOS_1 SSCM LINFlex_1 WKUP	I/O — I/O O I I	S	Tristate	26	37	45
PC[8]	PCR[40]	AF0 AF1 AF2 AF3	GPIO[40] LIN2TX E0UC[3] DEBUG[6]	SIUL LINFlex_2 eMIOS_0 SSCM	I/O O I/O O	S	Tristate	99	143	175
PC[9]	PCR[41]	AF0 AF1 AF2 AF3 — —	GPIO[41] — E0UC[7] DEBUG[7] WKUP[13][4] LIN2RX	SIUL — eMIOS_0 SSCM WKUP LINFlex_2	I/O — I/O O I I	S	Tristate	2	2	2
PC[10]	PCR[42]	AF0 AF1 AF2 AF3	GPIO[42] CAN1TX CAN4TX MA[1]	SIUL FlexCAN_1 FlexCAN_4 ADC_0	I/O O O O	M	Tristate	22	28	36
PC[11]	PCR[43]	AF0 AF1 AF2 AF3 — — —	GPIO[43] — — MA[2] WKUP[5][4] CAN1RX CAN4RX	SIUL — — ADC_0 WKUP FlexCAN_1 FlexCAN_4	I/O — — O I I I	S	Tristate	21	27	35
PC[12]	PCR[44]	AF0 AF1 AF2 AF3 — —	GPIO[44] E0UC[12] — — EIRQ[19] SIN_2	SIUL eMIOS_0 — — SIUL DSPI_2	I/O I/O — — I I	M	Tristate	97	141	173
PC[13]	PCR[45]	AF0 AF1 AF2 AF3	GPIO[45] E0UC[13] SOUT_2 —	SIUL eMIOS_0 DSPI_2 —	I/O I/O O —	S	Tristate	98	142	174

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 — —	GPIO[53] — — — ADC0_P[9] ADC1_P[9]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	46	68	82
PD[6]	PCR[54]	AF0 AF1 AF2 AF3 — —	GPIO[54] — — — ADC0_P[10] ADC1_P[10]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	47	69	83
PD[7]	PCR[55]	AF0 AF1 AF2 AF3 — —	GPIO[55] — — — ADC0_P[11] ADC1_P[11]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	48	70	84
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 — —	GPIO[56] — — — ADC0_P[12] ADC1_P[12]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	49	71	87
PD[9]	PCR[57]	AF0 AF1 AF2 AF3 — —	GPIO[57] — — — ADC0_P[13] ADC1_P[13]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	56	78	94
PD[10]	PCR[58]	AF0 AF1 AF2 AF3 — —	GPIO[58] — — — ADC0_P[14] ADC1_P[14]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	57	79	95
PD[11]	PCR[59]	AF0 AF1 AF2 AF3 — —	GPIO[59] — — — ADC0_P[15] ADC1_P[15]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	58	80	96
PD[12]	PCR[60]	AF0 AF1 AF2 AF3 —	GPIO[60] CS5_0 E0UC[24] — ADC0_S[4]	SIUL DSPI_0 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	—	—	100

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PE[6]	PCR[70]	AF0 AF1 AF2 AF3 —	GPIO[70] E0UC[22] CS3_0 MA[1] EIRQ[22]	SIUL eMIOS_0 DSPI_0 ADC_0 SIUL	I/O I/O O O I	M	Tristate	95	139	167
PE[7]	PCR[71]	AF0 AF1 AF2 AF3 —	GPIO[71] E0UC[23] CS2_0 MA[0] EIRQ[23]	SIUL eMIOS_0 DSPI_0 ADC_0 SIUL	I/O I/O O O I	M	Tristate	96	140	168
PE[8]	PCR[72]	AF0 AF1 AF2 AF3	GPIO[72] CAN2TX E0UC[22] CAN3TX	SIUL FlexCAN_2 eMIOS_0 FlexCAN_3	I/O O I/O O	M	Tristate	9	13	21
PE[9]	PCR[73]	AF0 AF1 AF2 AF3 — — —	GPIO[73] — E0UC[23] — WKUP[7][4] CAN2RX CAN3RX	SIUL — eMIOS_0 — WKUP FlexCAN_2 FlexCAN_3	I/O — I/O — I I I	S	Tristate	10	14	22
PE[10]	PCR[74]	AF0 AF1 AF2 AF3 —	GPIO[74] LIN3TX CS3_1 E1UC[30] EIRQ[10]	SIUL LINFlex_3 DSPI_1 eMIOS_1 SIUL	I/O O O I/O I	S	Tristate	11	15	23
PE[11]	PCR[75]	AF0 AF1 AF2 AF3 — —	GPIO[75] E0UC[24] CS4_1 — LIN3RX WKUP[14][4]	SIUL eMIOS_0 DSPI_1 — LINFlex_3 WKUP	I/O I/O O — I I	S	Tristate	13	17	25
PE[12]	PCR[76]	AF0 AF1 AF2 AF3 — — —	GPIO[76] — E1UC[19][10] — EIRQ[11] SIN_2 ADC1_S[7]	SIUL — eMIOS_1 — SIUL DSPI_2 ADC_1	I/O — I/O — I I I	J	Tristate	76	109	133
PE[13]	PCR[77]	AF0 AF1 AF2 AF3	GPIO[77] SOUT_2 E1UC[20] —	SIUL DSPI_2 eMIOS_1 —	I/O O I/O —	S	Tristate	—	103	127

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PF[7]	PCR[87]	AF0 AF1 AF2 AF3 —	GPIO[87] — CS2_1 — ADC0_S[15]	SIUL — DSPI_1 — ADC_0	I/O — O — I	J	Tristate	—	62	70
PF[8]	PCR[88]	AF0 AF1 AF2 AF3	GPIO[88] CAN3TX CS4_0 CAN2TX	SIUL FlexCAN_3 DSPI_0 FlexCAN_2	I/O O O O	M	Tristate	—	34	42
PF[9]	PCR[89]	AF0 AF1 AF2 AF3 — — —	GPIO[89] E1UC[1] CS5_0 — WKUP[22][4] CAN2RX CAN3RX	SIUL eMIOS_1 DSPI_0 — WKUP FlexCAN_2 FlexCAN_3	I/O I/O O — I I I	S	Tristate	—	33	41
PF[10]	PCR[90]	AF0 AF1 AF2 AF3	GPIO[90] CS1_0 LIN4TX E1UC[2]	SIUL DSPI_0 LINFlex_4 eMIOS_1	I/O O O I/O	M	Tristate	—	38	46
PF[11]	PCR[91]	AF0 AF1 AF2 AF3 — —	GPIO[91] CS2_0 E1UC[3] — WKUP[15][4] LIN4RX	SIUL DSPI_0 eMIOS_1 — WKUP LINFlex_4	I/O O I/O — I I	S	Tristate	—	39	47
PF[12]	PCR[92]	AF0 AF1 AF2 AF3	GPIO[92] E1UC[25] LIN5TX —	SIUL eMIOS_1 LINFlex_5 —	I/O I/O O —	M	Tristate	—	35	43
PF[13]	PCR[93]	AF0 AF1 AF2 AF3 — —	GPIO[93] E1UC[26] — — WKUP[16][4] LIN5RX	SIUL eMIOS_1 — — WKUP LINFlex_5	I/O I/O — — I I	S	Tristate	—	41	49
PF[14]	PCR[94]	AF0 AF1 AF2 AF3	GPIO[94] CAN4TX E1UC[27] CAN1TX	SIUL FlexCAN_4 eMIOS_1 FlexCAN_1	I/O O I/O O	M	Tristate	—	102	126

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PI[5]	PCR[133]	AF0 AF1 AF2 AF3	GPIO[133] E1UC[29] SCK_4 —	SIUL eMIOS_1 DSPI_4 —	I/O I/O I/O —	S	Tristate	—	—	142
PI[6]	PCR[134]	AF0 AF1 AF2 AF3	GPIO[134] E1UC[30] CS0_4 —	SIUL eMIOS_1 DSPI_4 —	I/O I/O I/O —	S	Tristate	—	—	11
PI[7]	PCR[135]	AF0 AF1 AF2 AF3	GPIO[135] E1UC[31] CS1_4 —	SIUL eMIOS_1 DSPI_4 —	I/O I/O I/O —	S	Tristate	—	—	12
PI[8]	PCR[136]	AF0 AF1 AF2 AF3 —	GPIO[136] — — — ADC0_S[16]	SIUL — — — ADC_0	I/O — — — I	J	Tristate	—	—	108
PI[9]	PCR[137]	AF0 AF1 AF2 AF3 —	GPIO[137] — — — ADC0_S[17]	SIUL — — — ADC_0	I/O — — — I	J	Tristate	—	—	109
PI[10]	PCR[138]	AF0 AF1 AF2 AF3 —	GPIO[138] — — — ADC0_S[18]	SIUL — — — ADC_0	I/O — — — I	J	Tristate	—	—	110
PI[11]	PCR[139]	AF0 AF1 AF2 AF3 — —	GPIO[139] — — — ADC0_S[19] SIN_3	SIUL — — — ADC_0 DSPI_3	I/O — — — I I	J	Tristate	—	—	111
PI[12]	PCR[140]	AF0 AF1 AF2 AF3 —	GPIO[140] CS0_3 — — ADC0_S[20]	SIUL DSPI_3 — — ADC_0	I/O I/O — — I	J	Tristate	—	—	112
PI[13]	PCR[141]	AF0 AF1 AF2 AF3 —	GPIO[141] CS1_3 — — ADC0_S[21]	SIUL DSPI_3 — — ADC_0	I/O I/O — — I	J	Tristate	—	—	113

K is a constant for the particular part, which may be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations 1 and 2 iteratively for any value of T_A.

3.6 I/O pad electrical characteristics

3.6.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads — are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads — provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads — provide maximum speed. These are used for improved debugging capability.
- Input only pads — are associated with ADC channels and 32 kHz low power external crystal oscillator providing low input leakage.

Medium and Fast pads can use slow configuration to reduce electromagnetic emission, at the cost of reducing AC performance.

3.6.2 I/O input DC characteristics

Table 12 provides input DC electrical characteristics as described in Figure 5.

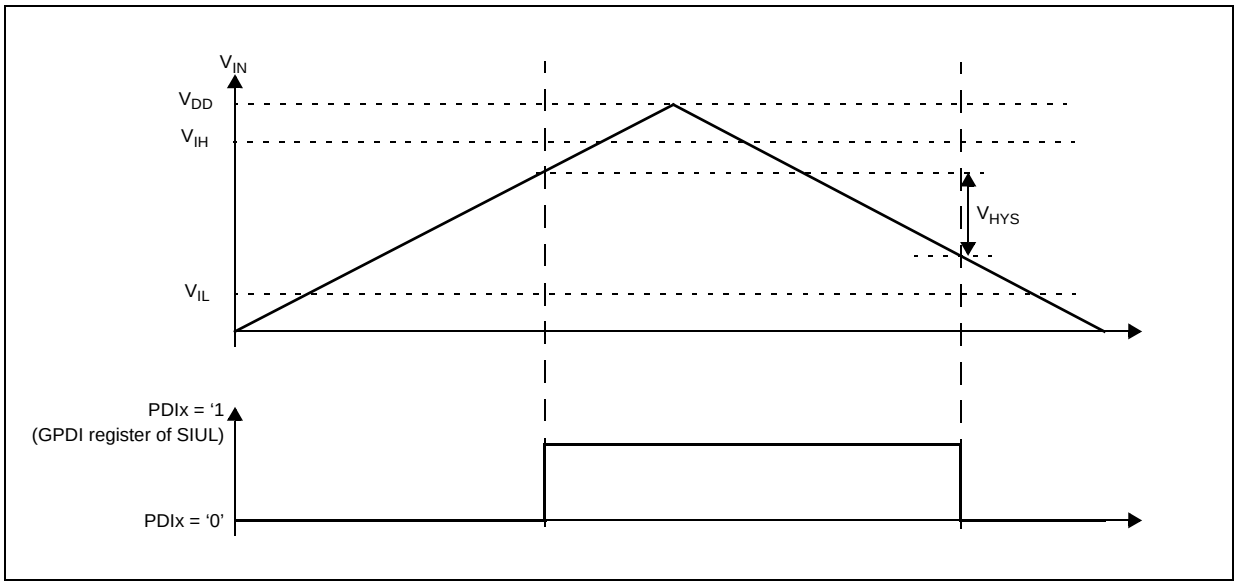

Figure 5. I/O input DC electrical characteristics definition

Table 12. I/O input DC electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
V_{IH}	SR	P	Input high level CMOS (Schmitt Trigger)	—		$0.65V_{DD}$	—	V_{DD} + 0.4	V
V_{IL}	SR	P	Input low level CMOS (Schmitt Trigger)	—		–0.4	—	$0.35V_{DD}$	
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—		$0.1V_{DD}$	—	—	
I_{LKG}	CC	P	Digital input leakage	No injection on adjacent pin	T_A = –40 °C	—	2	—	nA
		P			T_A = 25 °C	—	2	—	
		D			T_A = 85 °C	—	5	300	
		D			T_A = 105 °C	—	12	500	
		P			T_A = 125 °C	—	70	1000	
W_{FI}[2]	SR	P	Wakeup input filtered pulse	—		—	—	40	ns
W_{NFI}[2]	SR	P	Wakeup input not filtered pulse	—		1000	—	—	ns

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 In the range from 40 to 1000 ns, pulses can be filtered or not filtered, according to operating temperature and voltage.

3.6.3 I/O output DC characteristics

The following tables provide DC characteristics for bidirectional pads:

- Table 13 provides weak pull figures. Both pull-up and pull-down resistances are supported.
- Table 14 provides output driver characteristics for I/O pads when in SLOW configuration.
- Table 15 provides output driver characteristics for I/O pads when in MEDIUM configuration.
- Table 16 provides output driver characteristics for I/O pads when in FAST configuration.

Table 13. I/O pull-up/pull-down DC electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
$\lvert I_{WPU}\rvert$	CC	P	Weak pull-up current absolute value	V_{IN} = V_{IL}, V_{DD} = 5.0 V ± 10%	PAD3V5V = 0	10	—	150	µA
		C			PAD3V5V = 1[2]	10	—	250	
		P		V_{IN} = V_{IL}, V_{DD} = 3.3 V ± 10%	PAD3V5V = 1	10	—	150	
$\lvert I_{WPD}\rvert$	CC	P	Weak pull-down current absolute value	V_{IN} = V_{IH}, V_{DD} = 5.0 V ± 10%	PAD3V5V = 0	10	—	150	µA
		C			PAD3V5V = 1	10	—	250	
		P		V_{IN} = V_{IH}, V_{DD} = 3.3 V ± 10%	PAD3V5V = 1	10	—	150	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2 The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

Table 18. I/O supply segments

Package	Supply segment							
	1	2	3	4	5	6	7	8
176 LQFP	pin7 – pin27	pin28 – pin57	pin59 – pin85	pin86 – pin123	pin124 – pin150	pin151 – pin6	—	—
144 LQFP	pin20 – pin49	pin51 – pin99	pin100 – pin122	pin 123 – pin19	—	—	—	—
100 LQFP	pin16 – pin35	pin37 – pin69	pin70 – pin83	pin84 – pin15	—	—	—	—

Table 19. I/O consumption

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{SWTSLW}[2]	CC	D	Dynamic I/O current for SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	16	
I_{SWTMED}[2]	CC	D	Dynamic I/O current for MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	29	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	17	
I_{SWTFST}[2]	CC	D	Dynamic I/O current for FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	110	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	50	
I_{RMSSLW}	CC	D	Root medium square I/O current for SLOW configuration	C_L = 25 pF, 2 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	2.3	mA
				C_L = 25 pF, 4 MHz		—	—	3.2	
				C_L = 100 pF, 2 MHz		—	—	6.6	
				C_L = 25 pF, 2 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	1.6	
				C_L = 25 pF, 4 MHz		—	—	2.3	
				C_L = 100 pF, 2 MHz		—	—	4.7	
I_{RMSMED}	CC	D	Root medium square I/O current for MEDIUM configuration	C_L = 25 pF, 13 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	6.6	mA
				C_L = 25 pF, 40 MHz		—	—	13.4	
				C_L = 100 pF, 13 MHz		—	—	18.3	
				C_L = 25 pF, 13 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	5	
				C_L = 25 pF, 40 MHz		—	—	8.5	
				C_L = 100 pF, 13 MHz		—	—	11	

Table 20. I/O weight[1] (continued)

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
176 LQFP	144 LQFP	100 LQFP		SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
1	—	—	PH[15]	2%	3%	3%	3%	—	—	—	—
	—	—	PH[13]	3%	4%	3%	4%	—	—	—	—
	—	—	PH[14]	3%	4%	4%	4%	—	—	—	—
	—	—	PI[6]	4%	—	4%	—	—	—	—	—
	—	—	PI[7]	4%	—	4%	—	—	—	—	—
	4	—	PG[5]	4%	—	5%	—	10%	—	12%	—
		—	PG[4]	4%	6%	5%	5%	9%	13%	11%	12%
		—	PG[3]	4%	—	5%	—	9%	—	11%	—
		—	PG[2]	4%	6%	5%	5%	9%	12%	10%	11%
		4	PA[2]	4%	—	5%	—	8%	—	10%	—
			PE[0]	4%	—	5%	—	8%	—	9%	—
			PA[1]	4%	—	5%	—	8%	—	9%	—
			PE[1]	4%	6%	5%	6%	7%	10%	9%	9%
			PE[8]	4%	6%	5%	6%	7%	10%	8%	9%
			PE[9]	4%	—	5%	—	6%	—	8%	—
			PE[10]	4%	—	5%	—	6%	—	7%	—
			PA[0]	4%	6%	5%	5%	6%	8%	7%	7%
			PE[11]	4%	—	5%	—	5%	—	6%	—

Table 20. I/O weight[1] (continued)

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
176 LQFP	144 LQFP	100 LQFP		SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
2	1	—	PG[9]	9%	—	10%	—	9%	—	10%	—
		—	PG[8]	9%	—	11%	—	9%	—	11%	—
		1	PC[11]	9%	—	11%	—	9%	—	11%	—
			PC[10]	9%	13%	11%	12%	9%	13%	11%	12%
		—	PG[7]	9%	—	11%	—	9%	—	11%	—
		—	PG[6]	10%	14%	11%	12%	10%	14%	11%	12%
		1	PB[0]	10%	14%	12%	12%	10%	14%	12%	12%
			PB[1]	10%	—	12%	—	10%	—	12%	—
		—	PF[9]	10%	—	12%	—	10%	—	12%	—
		—	PF[8]	10%	14%	12%	13%	10%	14%	12%	13%
		—	PF[12]	10%	15%	12%	13%	10%	15%	12%	13%
		1	PC[6]	10%	—	12%	—	10%	—	12%	—
			PC[7]	10%	—	12%	—	10%	—	12%	—
		—	PF[10]	10%	14%	11%	12%	10%	14%	11%	12%
		—	PF[11]	9%	—	11%	—	9%	—	11%	—
		1	PA[15]	8%	12%	10%	10%	8%	12%	10%	10%
		—	PF[13]	8%	—	10%	—	8%	—	10%	—
		1	PA[14]	8%	11%	9%	10%	8%	11%	9%	10%
			PA[4]	7%	—	9%	—	7%	—	9%	—
			PA[13]	7%	10%	8%	9%	7%	10%	8%	9%
			PA[12]	7%	—	8%	—	7%	—	8%	—

Table 22. Voltage regulator electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
$I_{MREGINT}$	CC	D	Main regulator module current consumption	I_{MREG} = 200 mA	—	—	2	mA
				I_{MREG} = 0 mA	—	—	1	
V_{LPREG}	CC	P	Low power regulator output voltage	After trimming	1.15	1.23	1.32	V
I_{LPREG}	SR	—	Low power regulator current provided to V_{DD_LV} domain	—	—	—	15	mA
$I_{LPREGINT}$	CC	D	Low power regulator module current consumption	I_{LPREG} = 15 mA; T_A = 55 °C	—	—	600	µA
		—		I_{LPREG} = 0 mA; T_A = 55 °C	—	5	—	
V_{ULPREG}	CC	P	Ultra low power regulator output voltage	After trimming	1.15	1.23	1.32	V
I_{ULPREG}	SR	—	Ultra low power regulator current provided to V_{DD_LV} domain	—	—	—	5	mA
$I_{ULPREGINT}$	CC	D	Ultra low power regulator module current consumption	I_{ULPREG} = 5 mA; T_A = 55 °C	—	—	100	µA
				I_{ULPREG} = 0 mA; T_A = 55 °C	—	2	—	
I_{DD_BV}	CC	D	Inrush average current on V_{DD_BV} during power-up[5]	—	—	—	300[6]	mA
$\left\|\frac{d}{dt}VDD\right\|$	SR	—	Maximum slope on VDD	—	—	—	250	mV/µs
$\|\Delta_{VDD(STDBY))}\|$	SR	—	Maximum instant variation on VDD during STANDBY exit	—	—	—	30	mV
$\left\|\frac{d}{dt}VDD(STDBY)\right\|$	SR	—	Maximum slope on VDD during STANDBY exit	—	—	—	15	mV/µs

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 This capacitance value is driven by the constraints of the external voltage regulator supplying the V_{DD_BV} voltage. A typical value is in the range of 470 nF.

3 This value is acceptable to guarantee operation from 4.5 V to 5.5 V

4 External regulator and capacitance circuitry must be capable of providing I_{DD_BV} while maintaining supply V_{DD_BV} in operating range.

5 Inrush current is seen only for short time during power-up and on standby exit (max 20 µs, depending on external capacitances to be load).

6 The duration of the inrush current depends on the capacitance placed on LV pins. BV decoupling capacitors must be sized accordingly. Refer to I_{MREG} value for minimum amount of current to be provided in cc.

3.8.2 Voltage monitor electrical characteristics

The device implements a Power-on Reset module to ensure correct power-up initialization, as well as four low voltage detectors to monitor the V_{DD} and the V_{DD_LV} voltage while device is supplied:

Therefore it is recommended that the user apply EMC software optimization and prequalification tests in relation with the EMC level requested for the application.

- Software recommendations – The software flowchart must include the management of runaway conditions such as:
  - Corrupted program counter
  - Unexpected reset
  - Critical data corruption (control registers...)
- Prequalification trials – Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the reset pin or the oscillator pins for 1 second.

  To complete these trials, ESD stress can be applied directly on the device. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring.

3.11.2 Electromagnetic interference (EMI)

The product is monitored in terms of emission based on a typical application. This emission test conforms to the IEC61967-1 standard, which specifies the general conditions for EMI measurements.

Table 30. EMI radiated emission measurement[1,2]

Symbol		C	Parameter	Conditions		Value			Unit
						Min	Typ	Max	
—	SR	—	Scan range	—		0.150		1000	MHz
f_{CPU}	SR	—	Operating frequency	—		—	64	—	MHz
V_{DD_LV}	SR	—	LV operating voltages	—		—	1.28	—	V
S_{EMI}	CC	T	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP144 package Test conforming to IEC 61967-2, f_{OSC} = 8 MHz/f_{CPU} = 64 MHz	No PLL frequency modulation	—	—	18	dBµV
					± 2% PLL frequency modulation	—	—	14	dBµV

1 EMI testing and I/O port waveforms per IEC 61967-1, -2, -4

2 For information on conducted emission and susceptibility measurement (norm IEC 61967-4), please contact your local marketing representative.

3.11.3 Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity.

3.11.3.1 Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts×(n + 1) supply pin). This test conforms to the AEC-Q100-002/-003/-011 standard.

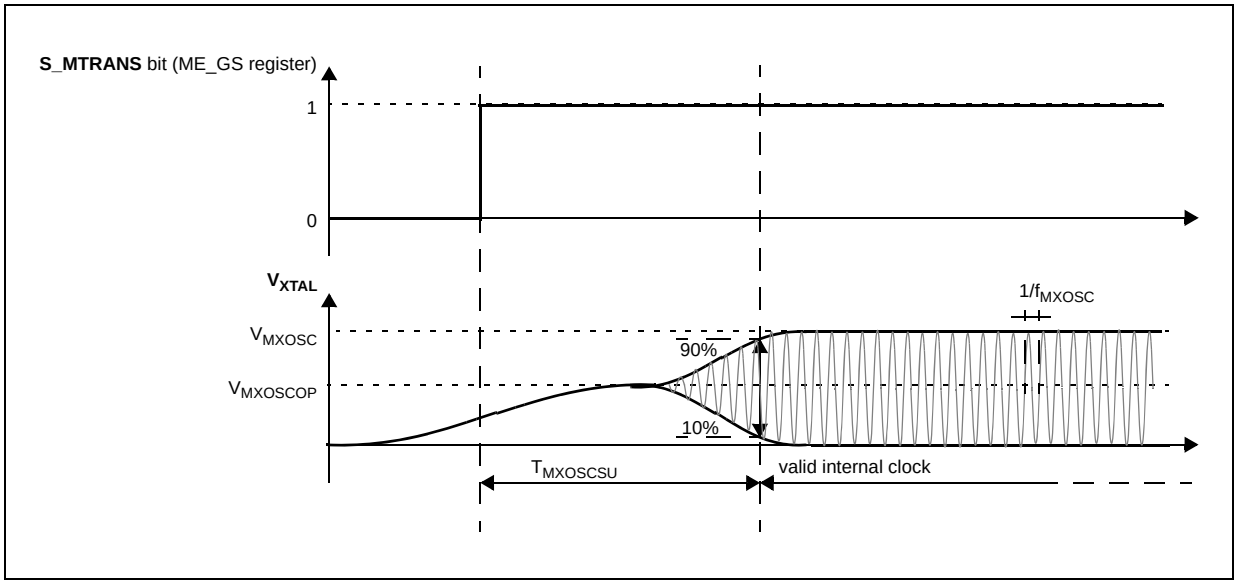

Figure 13. Fast external crystal oscillator (4 to 16 MHz) electrical characteristics

Table 34. Fast external crystal oscillator (4 to 16 MHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
f_{FXOSC}	SR	—	Fast external crystal oscillator frequency	—	4.0	—	16.0	MHz
g_{mFXOSC}	CC	C	Fast external crystal oscillator transconductance	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 OSCILLATOR_MARGIN = 0	2.2	—	8.2	mA/V
	CC	P		V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 OSCILLATOR_MARGIN = 0	2.0	—	7.4	
	CC	C		V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 OSCILLATOR_MARGIN = 1	2.7	—	9.7	
	CC	C		V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 OSCILLATOR_MARGIN = 1	2.5	—	9.2	
V_{FXOSC}	CC	T	Oscillation amplitude at EXTAL	f_{OSC} = 4 MHz, OSCILLATOR_MARGIN = 0	1.3	—	—	V
				f_{OSC} = 16 MHz, OSCILLATOR_MARGIN = 1	1.3	—	—	
$V_{FXOSCOP}$	CC	P	Oscillation operating point	—	—	0.95		V
I_{FXOSC}[2]	CC	T	Fast external crystal oscillator consumption	—	—	2	3	mA

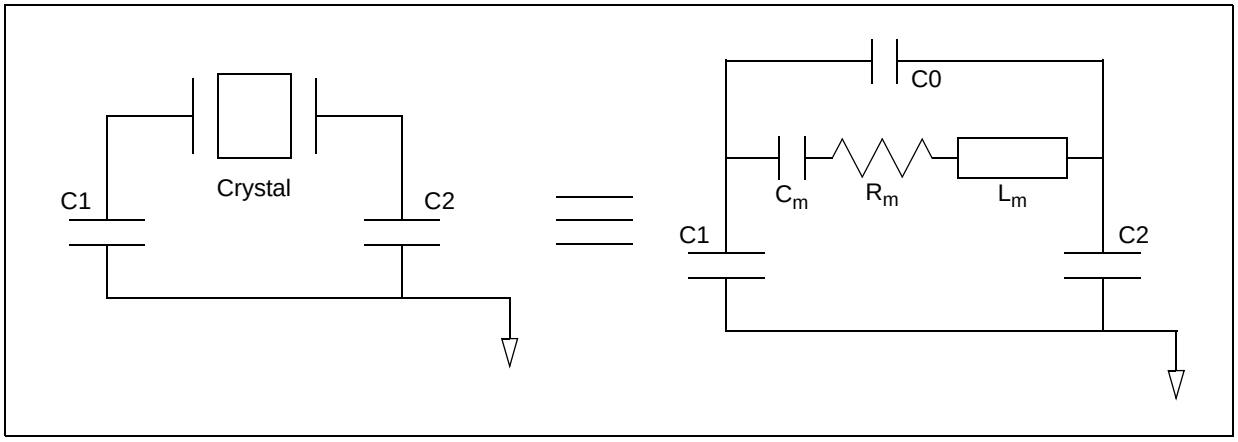

Figure 15. Equivalent circuit of a quartz crystal

Table 35. Crystal motional characteristics[1]

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
L_m	Motional inductance	—	—	11.796	—	KH
C_m	Motional capacitance	—	—	2	—	fF
C1/C2	Load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground[2]	—	18	—	28	pF
R_m[3]	Motional resistance	AC coupled at C0 = 2.85 pF[4]	—	—	65	kΩ
		AC coupled at C0 = 4.9 pF[4]	—	—	50	
		AC coupled at C0 = 7.0 pF[4]	—	—	35	
		AC coupled at C0 = 9.0 pF[4]	—	—	30	

1 The crystal used is Epson Toyocom MC306.

2 This is the recommended range of load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground. It includes all the parasitics due to board traces, crystal and package.

3 Maximum ESR (R_m) of the crystal is 50 kΩ

4 C0 Includes a parasitic capacitance of 2.0 pF between OSC32K_XTAL and OSC32K_EXTAL pins.

Table 37. FMPLL electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
f_{PLLOUT}	CC	P	FMPLL output clock frequency	—	16	—	64	MHz
f_{VCO}[3]	CC	P	VCO frequency without frequency modulation	—	256	—	512	MHz
		P	VCO frequency with frequency modulation	—	245.76	—	532.48	
f_{CPU}	SR	—	System clock frequency	—	—	—	64[4]	MHz
f_{FREE}	CC	P	Free-running frequency	—	20	—	150	MHz
t_{LOCK}	CC	P	FMPLL lock time	Stable oscillator (f_{PLLIN} = 16 MHz)		40	100	µs
Δt_{STJIT}	CC	—	FMPLL short term jitter[5]	f_{sys} maximum	–4	—	4	%
Δt_{LTJIT}	CC	—	FMPLL long term jitter	f_{PLLCLK} at 64 MHz, 4000 cycles	—	—	10	ns
I_{PLL}	CC	C	FMPLL consumption	T_A = 25 °C	—	—	4	mA

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 PLLIN clock retrieved directly from FXOSC clock. Input characteristics are granted when oscillator is used in functional mode. When bypass mode is used, oscillator input clock should verify f_{PLLIN} and Δ_{PLLIN}.

3 Frequency modulation is considered ± 4%.

4 f_{CPU} 64 MHz can be achieved only at up to 105 °C.

5 Short term jitter is measured on the clock rising edge at cycle *n* and *n* + 4.

3.15 Fast internal RC oscillator (16 MHz) electrical characteristics

The device provides a 16 MHz main internal RC oscillator. This is used as the default clock at the power-up of the device.

Table 38. Fast internal RC oscillator (16 MHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
f_{FIRC}	CC	P	Fast internal RC oscillator high frequency	T_A = 25 °C, trimmed		—	16	—	MHz
	SR	—		—		12		20	
$I_{FIRCRUN}$[2],	CC	T	Fast internal RC oscillator high frequency current in running mode	T_A = 25 °C, trimmed		—	—	200	µA
$I_{FIRCPWD}$	CC	D	Fast internal RC oscillator high frequency current in power down mode	T_A = 25 °C		—	—	10	µA
$I_{FIRCSTOP}$	CC	T	Fast internal RC oscillator high frequency and system clock current in stop mode	T_A = 25 °C	sysclk = off	—	500	—	µA
					sysclk = 2 MHz	—	600	—	
					sysclk = 4 MHz	—	700	—	
					sysclk = 8 MHz	—	900	—	
					sysclk = 16 MHz	—	1250	—	

possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: C_S being substantially a switched capacitance, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_S equal to 3 pF, a resistance of 330 kΩ is obtained ($R_{EQ} = 1 / (fc \times C_S)$, where fc represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_S) and the sum of $R_S + R_F + R_L + R_{SW} + R_{AD}$, the external circuit must be designed to respect the Equation 4:

Eqn. 4

$$V_A \bullet \frac{R_S + R_F + R_L + R_{SW} + R_{AD}}{R_{EQ}} < \frac{1}{2} LSB$$

Equation 4 generates a constraint for external network design, in particular on resistive path. Internal switch resistances (R_{SW} and R_{AD}) can be neglected with respect to external resistances.

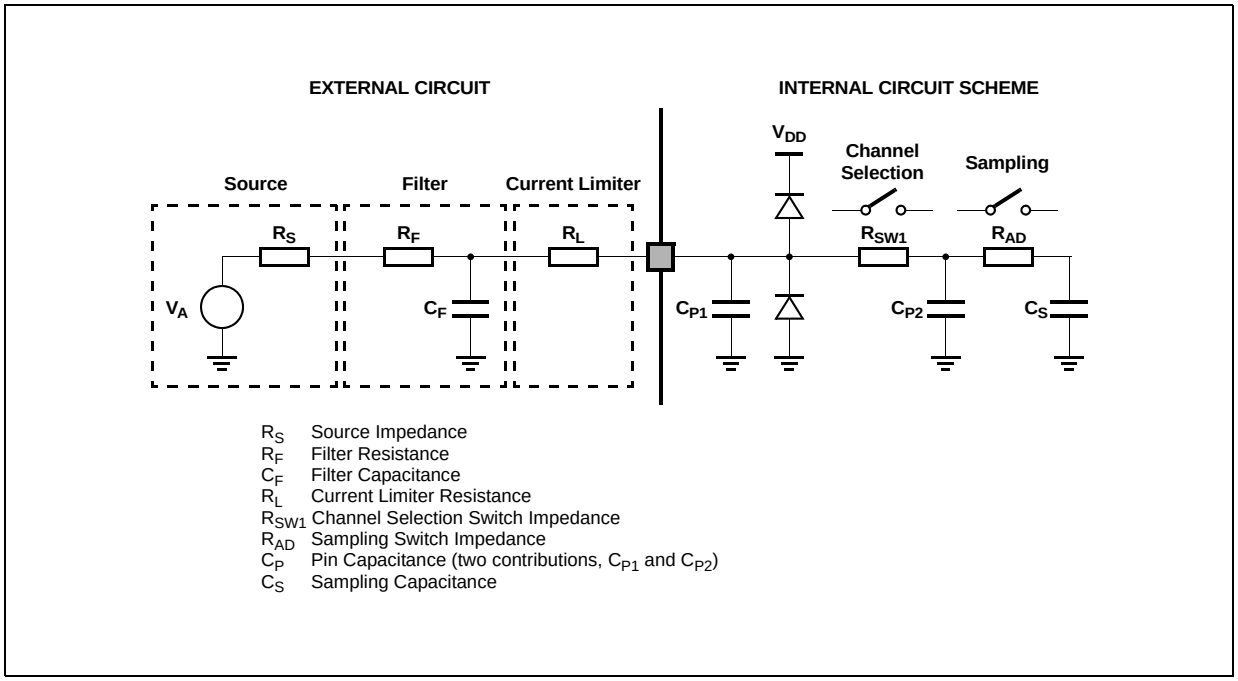

Figure 18. Input equivalent circuit (precise channels)

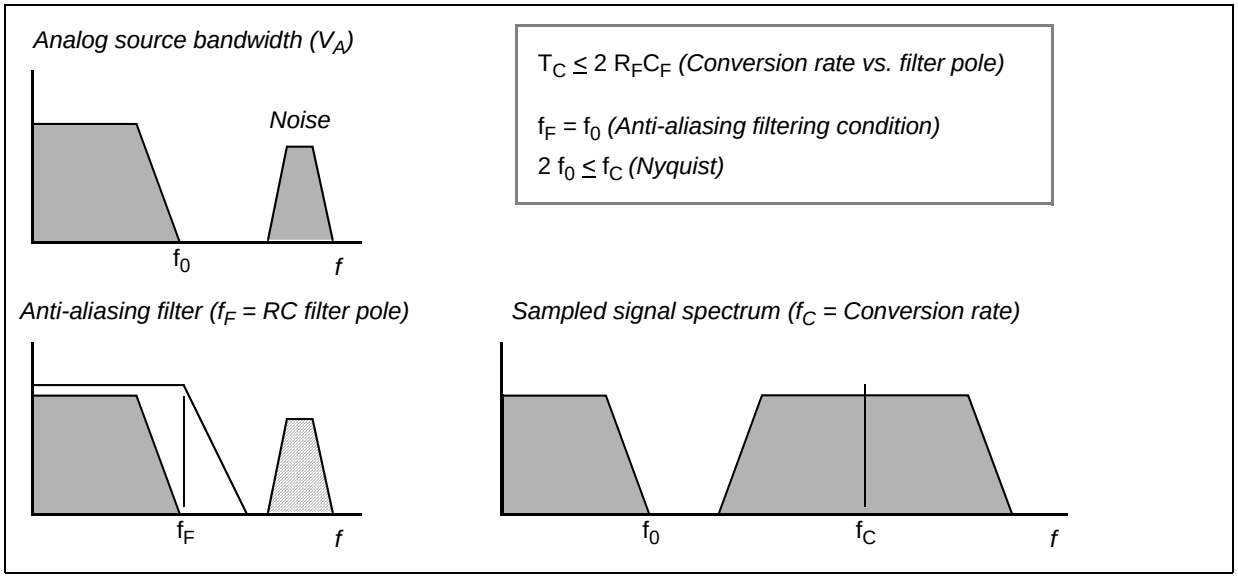

Figure 21. Spectral representation of input signal

Calling f_0 the bandwidth of the source signal (and as a consequence the cut-off frequency of the antialiasing filter, f_F), according to the Nyquist theorem the conversion rate f_C must be at least $2f_0$; it means that the constant time of the filter is greater than or at least equal to twice the conversion period (T_C). Again the conversion period T_C is longer than the sampling time T_S, which is just a portion of it, even when fixed channel continuous conversion mode is selected (fastest conversion rate at a specific channel): in conclusion it is evident that the time constant of the filter $R_F C_F$ is definitively much higher than the sampling time T_S, so the charge level on C_S cannot be modified by the analog signal source during the time in which the sampling switch is closed.

The considerations above lead to impose new constraints on the external circuit, to reduce the accuracy error due to the voltage drop on C_S; from the two charge balance equations above, it is simple to derive Equation 11 between the ideal and real sampled voltage on C_S:

Eqn. 11

$$\frac{V_{A2}}{V_A} = \frac{C_{P1} + C_{P2} + C_F}{C_{P1} + C_{P2} + C_F + C_S}$$

From this formula, in the worst case (when V_A is maximum, that is for instance 5 V), assuming to accept a maximum error of half a count, a constraint is evident on C_F value:

ADC_0 (10-bit) ***Eqn. 12***

$$C_F > 2048 \bullet C_S$$

ADC_1 (12-bit) ***Eqn. 13***

$$C_F > 8192 \bullet C_S$$

Table 43. On-chip peripherals current consumption[1] (continued)

Symbol		C	Parameter	Conditions		Value	Unit
						Typ	
$I_{DD\_HV\_ADC1}$	CC	T	ADC_1 supply current on $V_{DD\_HV\_ADC1}$	V_{DD} = 5.5 V	Analog static consumption (no conversion)	300 * f_{periph}	µA
				V_{DD} = 5.5 V	Analog dynamic consumption (continuous conversion)	4	mA
$I_{DD\_HV(FLASH)}$	CC	T	CFlash + DFlash supply current on V_{DD_HV}	V_{DD} = 5.5 V	—	12	mA
$I_{DD\_BV(PLL)}$	CC	T	PLL supply current on V_{DD_BV}	V_{DD} = 5.5 V	—	2.5	mA

1 Operating conditions: T_A = 25 °C, f_{periph} = 8 MHz to 64 MHz

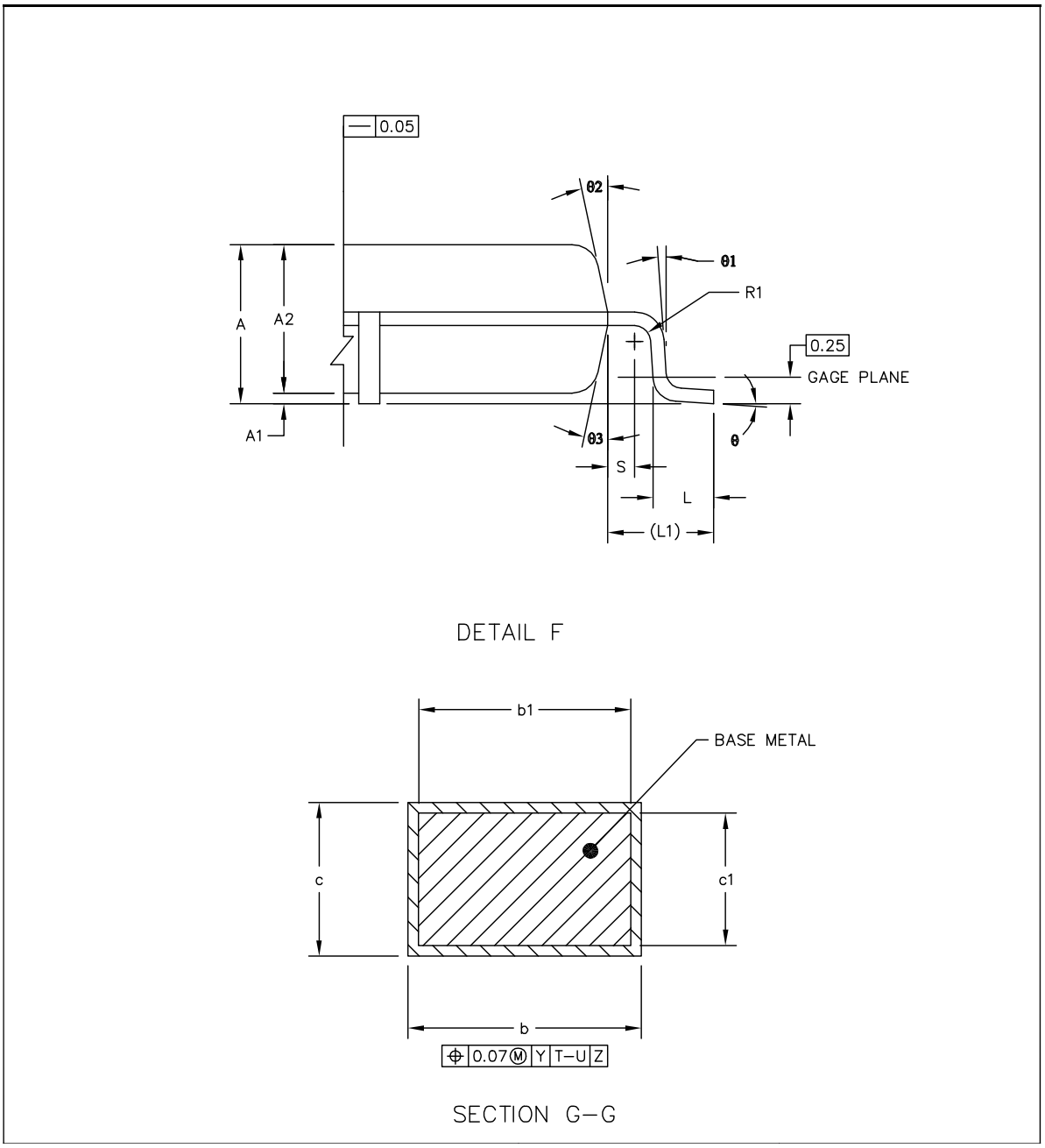

Figure 34. 176 LQFP package mechanical drawing (Part 2 of 3)

Table 46. Revision history (continued)

Revision	Date	Description of changes
2 (cont.)	15 May 2013	In Table 24 (Electrical characteristics in different application modes), — Changed I_{DDMAX} Typ to 81 mA and I_{DDMAX} Typ to 130 mA. — Changed I_{DDRUN} Typ for fCPU = 32 MHz to 40 mA. — Changed I_{DDRUN} Typ for fCPU = 48 MHz to 54 mA. Added I_{DDRUN} Max of 96 mA. — Changed I_{DDRUN} Typ for fCPU = 64 MHz to 67 mA. Added I_{DDRUN} Max of 120 mA. — Changed I_{DDHALT} at T_A = 25 °C Typ to 10 mA and I_{DDHALT} Max to 15 mA. — Changed I_{DDHALT} at T_A = 125 °C Typ to 15 mA and I_{DDHALT} Max to 28 mA. — Changed I_{DDSTOP} T_A temperature from –40 °C to 25 °C. — Changed I_{DDSTOP} at T_A = 25 °C Typ to 130 µA and I_{DDSTOP} Max to 500 µA. — Changed I_{DDSTOP} at T_A = 55 °C Typ to 180 µA. — Changed I_{DDSTOP} at T_A = 85 °C Typ to 1 mA and I_{DDSTOP} Max to 5 mA. — Changed I_{DDSTOP} at T_A = 105 °C Typ to 3 mA and I_{DDSTOP} Max to 9 mA. — Changed I_{DDSTOP} at T_A = 125 °C Typ to 5 mA and I_{DDSTOP} Max to 14 mA. — Changed $I_{DDSTDBY2}$ at T_A = 25 °C Typ to 17 µA and Max to 80 µA. — Changed $I_{DDSTDBY2}$ at T_A = 55 °C Typ to 30 µA. — Changed $I_{DDSTDBY2}$ at T_A = 85 °C Typ to 100 µA. — Changed $I_{DDSTDBY2}$ at T_A = 105 °C Typ to 280 µA and Max to 950 µA. — Changed $I_{DDSTDBY2}$ at T_A = 125 °C Typ to 460 µA and Max to 1700 µA. — Changed the parameter classification for $I_{DDSTANDBY2}$ (T_A = 125 °C) — Changed $I_{DDSTDBY1}$ at T_A = 25 °C Typ to 12 µA and Max to 50 µA. — Changed $I_{DDSTDBY1}$ at T_A = 55 °C Typ to 24 µA. — Changed $I_{DDSTDBY1}$ at T_A = 85 °C Typ to 48 µA. — Changed $I_{DDSTDBY1}$ at T_A = 105 °C Typ to 150 µA and Max to 500 µA. — Changed $I_{DDSTDBY1}$ at T_A = 125 °C Typ to 260 µA. — Changed the third sentence of Footnote 3 to begin with “The given value is thought to be a **worst case value** (64 MHz at 125 °C) with all peripherals running.” — Removed footnotes 8 and 9 regarding I_{DDHALT} and I_{DDSTOP}. — Corrected “C” characteristics to reflect testing status. In Section 3.10, Flash memory electrical characteristics, removed the "FLASH_BIU settings vs. frequency of operation" table. In Table 28 (Flash power supply DC electrical characteristics), corrected Footnote 2 to specify 125 °C. In Section 3.14, FMPLL electrical characteristics, changed the text “the main oscillator driver” to “the FXOSC or FIRC sources.” In Table 40 (ADC input leakage current), added specifications for 85 °C. In Table 44 (DSPI characteristics), added t_{SCK} specifications for MTFE=1. In Table 44 (DSPI characteristics), updated specifications 7 and 8 to 13 ns, all DSPIs. in ADC section, corrected Equation 11. In Figure 41 (Commercial product code structure), added “**Note:** Not all options are available on all devices.” Removed Section 6, Abbreviations.
3	11 Sep 2013	Updated the temperature in table note 2 in Table 1 (MPC5606BK family comparison) from 105 ^{o}C to 125 ^{o}C.
4	25 Nov 2015	Updated the Max value current for $I_{ADC0run}$ from 40 mA to 5 mA in Table 41 (ADC_0 conversion characteristics (10-bit ADC_0))